

# Silicon Carbide Diode

Rev.01 - 07 March 2022

**Product data sheet** 

### **1. General description**

Dual Silicon Carbide Schottky diode in a TO247-3L plastic package, designed for high frequency switched-mode power supplies.

### 2. Features and benefits

- Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T<sub>i(max)</sub> = 175 °C)

#### 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage			12	200		V
I <sub>O(AV)</sub>	limiting average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 119 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	40		A		
T <sub>j</sub>	junction temperature		·	175		°C	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.45	1.65	V
		$I_F = 20 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 5$		-	1.95	2.30	V
		$I_F = 20 \text{ A}; T_j = 175 \text{ °C}; \text{ per diode}; Fig. 5$		-	2.10	2.60	V
Dynamic	characteristics						
Q <sub>r</sub>	recovered charge	$I_F = 20 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	44	-	nC



# **5. Pinning information**

Table 2. F	Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	К	cathode		
3	A2	anode		К К
mb	mb	mounting base; connected to cathode		sym125

# 6. Ordering information

Table 3. Ordering information							
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
WNSC2D401200CW	TO247	WNSC2D401200CW6Q	Tube	30	SOT429	25-Mar-2013	

### 7. Marking

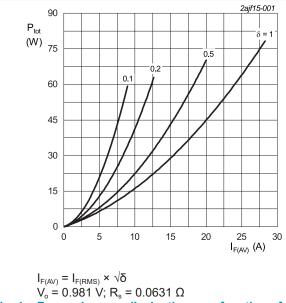
Table 4. Marking codes						
Type number	Marking codes					
WNSC2D401200CW	WNSC2D 401200CW					

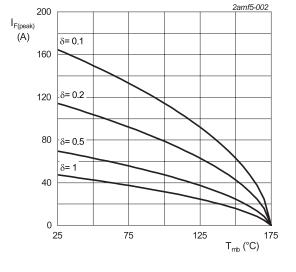
### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		1200	V
$V_{\text{RWM}}$	crest working reverse voltage		1200	V
V <sub>R</sub>	reverse voltage	DC	1200	V
I <sub>O(AV)</sub>	limiting average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 119$ °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	40	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 119 °C; square-wave pulse; per diode	40	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	160	A
		$t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode	1000	A
l <sup>2</sup> t	l <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms	128	A²s
T <sub>stg</sub>	storage temperature		-55 to 175	°C
T <sub>j</sub>	junction temperature		-55 to 175	°C



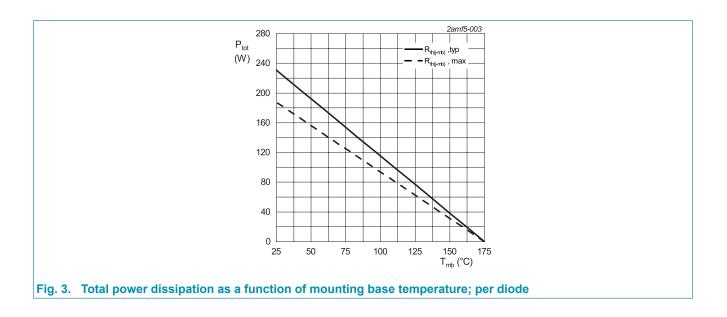




I<sub>F(AV)</sub> = I<sub>F(RMS)</sub> × √δ
V<sub>o</sub> = 0.981 V; R<sub>s</sub> = 0.0631 Ω
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

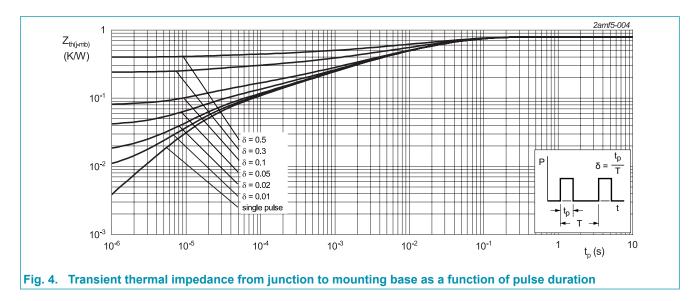
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#### WNSC2D401200CW Silicon Carbide Diode



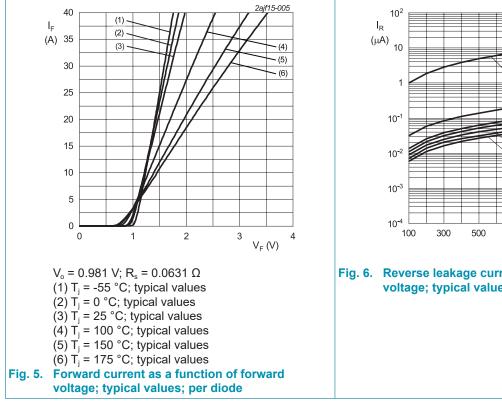
# 9. Thermal characteristics

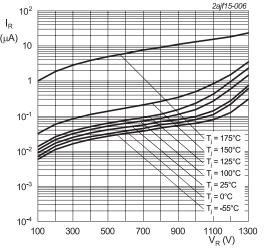
Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	per diode; <u>Fig. 4</u>	-	0.65	0.8	K/W
		both diodes conducting	-	0.31	0.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W



### **10. Characteristics**

Table 7. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward current	$I_{F} = 20 \text{ A}; T_{j} = 25 \text{ °C}; \text{ per diode}; Fig. 5$	-	1.45	1.65	V
		$I_F = 20 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 5$	-	1.95	2.30	V
		$I_F = 20 \text{ A}; T_j = 175 \text{ °C}; \text{ per diode}; Fig. 5$	-	2.10	2.60	V
I <sub>R</sub>	reverse current	$V_{R}$ = 1200 V; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	1	100	μA
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>	-	25	1000	μA
Dynamic	characteristics		· /			
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 20 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 7</u>	-	44	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; $V_R$ = 1 V; $T_j$ = 25 °C; per diode	-	927	-	pF
		f = 1 MHz; $V_R$ = 400 V; $T_j$ = 25 °C; per diode	-	84	-	pF
		f = 1 MHz; $V_R$ = 800 V; $T_j$ = 25 °C; per diode	-	63	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	$I_R$ = 5.3 A; L = 10 mH; $T_{j(init)}$ = 25 °C; per diode	140	-	-	mJ

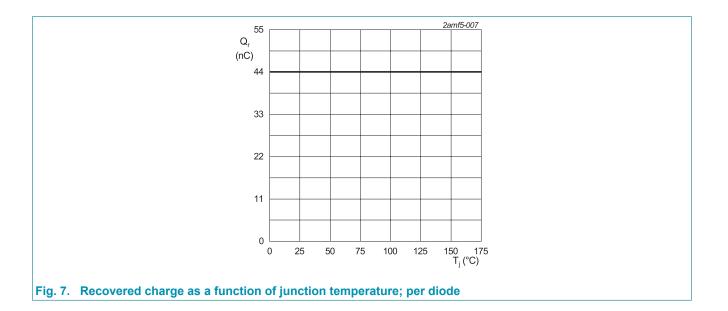






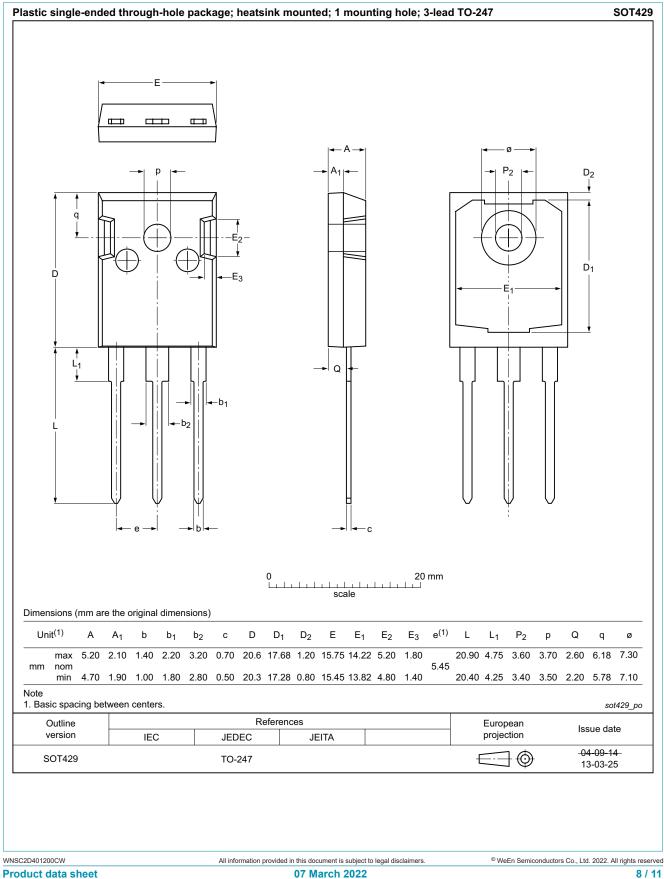
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### 11. Package outline



#### Silicon Carbide Diode

# 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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